

2SJ486 Silicon P Channel MOS FET

REJ03G0869-0300 (Previous: ADE-208-512A) Rev.3.00 Sep 07, 2005

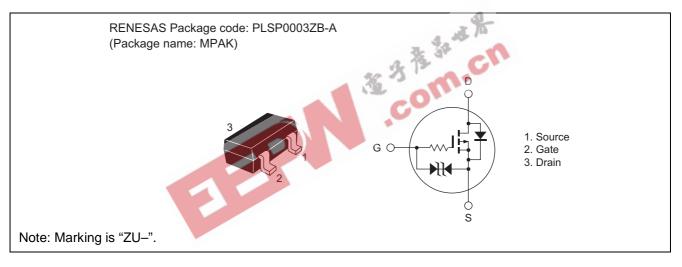
Description

Low frequency power switching

Features

- Low on-resistance $R_{DS\;(on)}=0.5\;\Omega\;typ.\;(at\;V_{GS}=-4\;V,\,I_D=-100\;mA)$
- 2.5 V gate drive devices.
- Small package (MPAK).

Outline





Absolute Maximum Ratings

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	-30	V
Gate to source voltage	V _{GSS}	±10	V
Drain current	ID	-0.3	А
Drain peak current	I _{D (pulse)} Note 1	-0.6	А
Channel dissipation	Pch	150	mW
Channel temperature	Tch	150	٥°
Storage temperature	Tstg	-55 to +150	°C

 $(Ta = 25^{\circ}C)$

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Note: 1. PW \leq 100 μ s, duty cycle \leq 10%

Electrical Characteristics

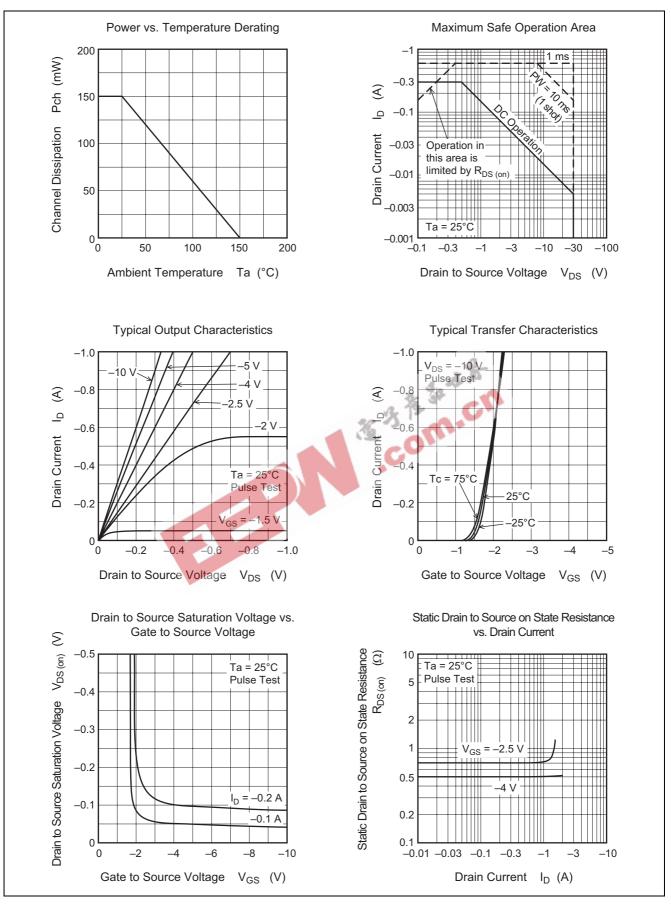
Min **Test Conditions** Item Symbol Max Unit Тур Drain to source breakdown voltage V (BR) DSS -30 V $I_D = -10 \ \mu A, \ V_{GS} = 0$ ____ ____ V Gate to source breakdown voltage V (BR) GSS ±10 $I_G=\pm 100~\mu A,~V_{DS}=0$ _ _ $V_{DS} = -30 \text{ V}, \ V_{GS} = 0$ Zero gate voltage drain current -1.0 μΑ I_{DSS} — _ Gate to source leak current ±5.0 $V_{GS}=\pm6.5~V,~V_{DS}=0$ I_{GSS} ___ _ μΑ $I_D = -10 \ \mu A, V_{DS} = -5 \ V$ Gate to source cutoff voltage -0.5 -1.5 V V_{GS (off)} ____ $I_D = -100 \text{ mA}, V_{GS} = -4 \text{ V}^{Note 2}$ Static drain to source on state resistance 0.5 0.65 Ω R_{DS (on)} ____ $V_{GS} = -100 \text{ mA}, V_{GS} = -2.5 \text{ V}^{\text{Note 2}}$ _ 0.7 1.2 Ω R_{DS (on)} $I_{\rm D} = -100$ mA, $V_{\rm DS} = -10$ V ^{Note 2} Forward transfer admittance y_{fs} 0.4 0.65 ÷ S 45 $V_{DS} = -10 V$ Input capacitance Ciss ____ pF 76 Coss 1 $V_{GS} = 0$ Output capacitance pF -Reverse transfer capacitance Crss 5.4 pF f = 1 MHz-Turn-on delay time $V_{GS} = -4 V$ t_{d (on)} 120 ____ ns $I_{D} = -150 \text{ mA}$ Rise time tr 340 _ ns $R_L = 66.6 \Omega$ Turn-off delay time 850 ____ ns td (off) ____ 550 Fall time ____ ____ tf ns

Note: 2. Pulse test

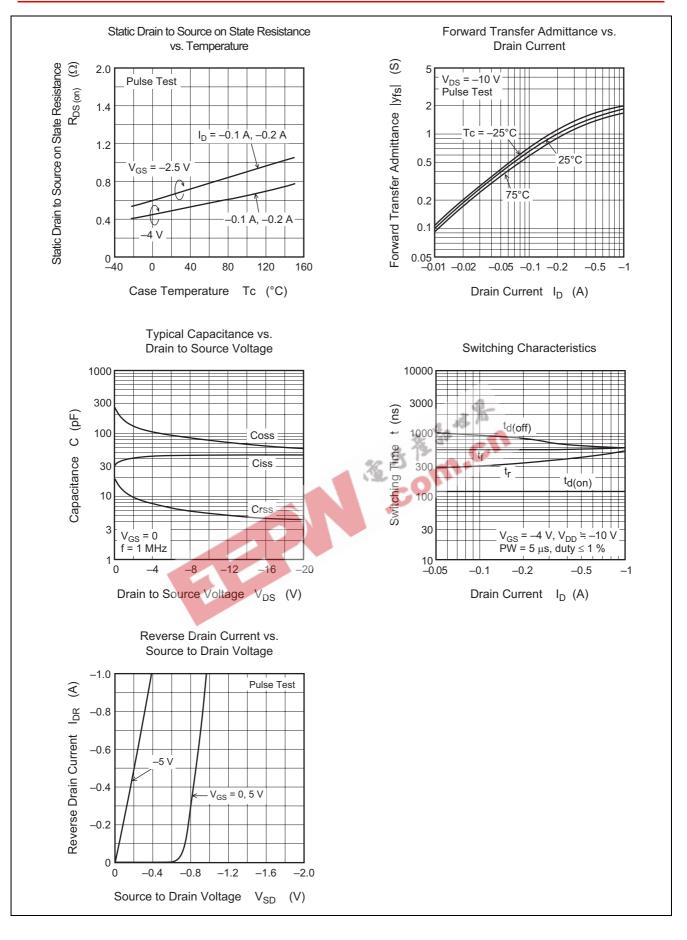
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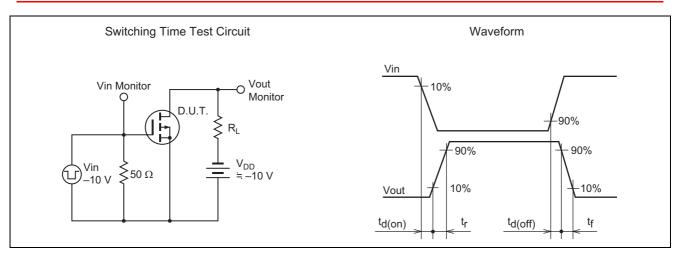
Main Characteristics







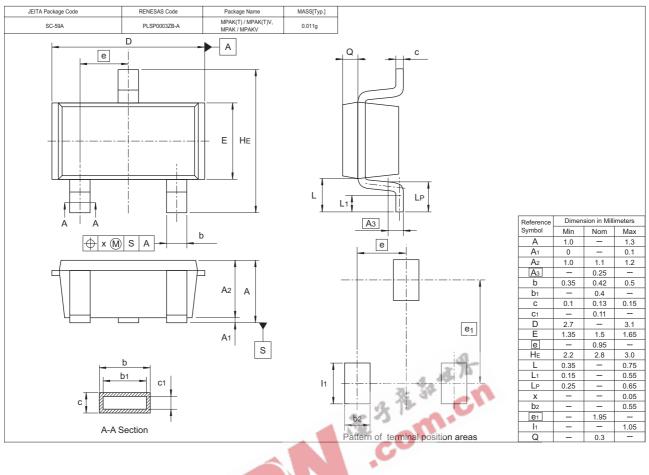








Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SJ486ZU-TL-E	3000 pcs	Taping
2SJ486ZU-TR-E	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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